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(Signature & date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of :

May 4, 2004

Khater, et al. :

Group Art Unit: To Be Assigned

Serial No: 10/709,220 :

Examiner: To Be Assigned

Filed: 4/22/04 :

International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: STRUCTURE AND METHOD OF FORMING BIPOLAR TRANSISTOR HAVING A SELF-
ALIGNED RAISED EXTRINSIC BASE USING SELF-ALIGNED ETCH STOP LAYER

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

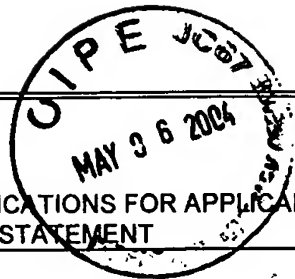
In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,
Khater, et al.

By 

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FORM PTO-1449 (Modified)	ATTY. DOCKET NO. FIS920030412US1	SERIAL NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT: KHATER ET AL.	
(Use several sheets if necessary)	FILING DATE:	GROUP:

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	ISSUED DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

CA	Jagannathan, et al., "Self-aligned SiGe NPN Transistors with 285 GHz f_{MAX} and 207 GHz f_T in a Manufacturable Technology," IEEE Electron Device Letters 23, 258 (2002)
CB	J.S. Rieh, et al., "SiGe HBTs with Cut-off Frequency of 350 GHz," International Electron Device Meeting Technical Digest, 771 (2002)

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.